Ordering number : ENA1547A

SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

ATP201 — General-Purpose Switching Device Applications

Features

- Low ON-resistance
- Slim package
- Protection diode in
- 4.5V drive
- Halogen free compliance

Specifications

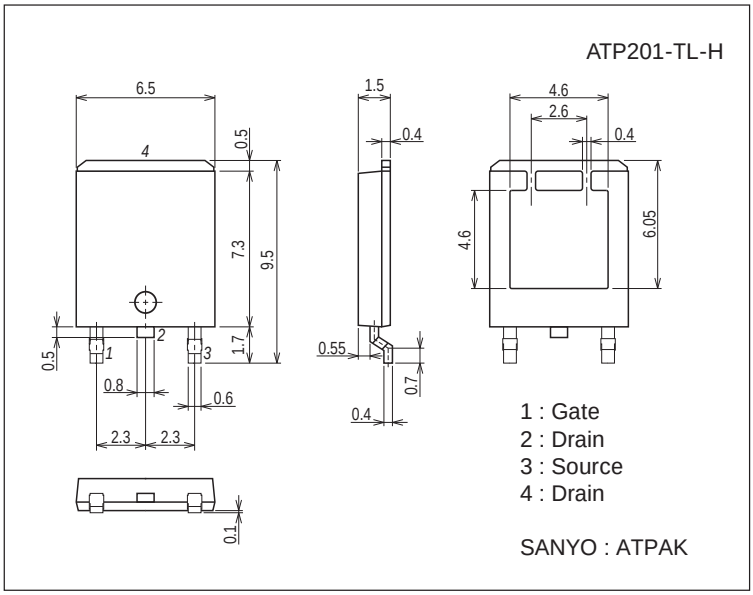
Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DSS}		30	V
Gate-to-Source Voltage	V_{GSS}		±20	V
Drain Current (DC)	I_D		35	A
Drain Current (PW≤10μs)	I_{DP}	PW≤10μs, duty cycle≤1%	105	A
Allowable Power Dissipation	P_D	Tc=25°C	30	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		−55 to +150	°C
Avalanche Energy (Single Pulse) *1	E_{AS}		10	mJ
Avalanche Current *2	I_{AV}		18	A

Note :*1 V_{DD}=10V, L=50μH, I_{AV}=18A
*2 L≤50μH, Single pulse

Package Dimensions

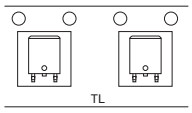
unit : mm (typ)
7057-001



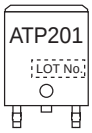
Product & Package Information

- Package : ATPAK
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

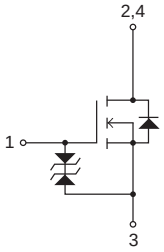
Packing Type: TL



Marking



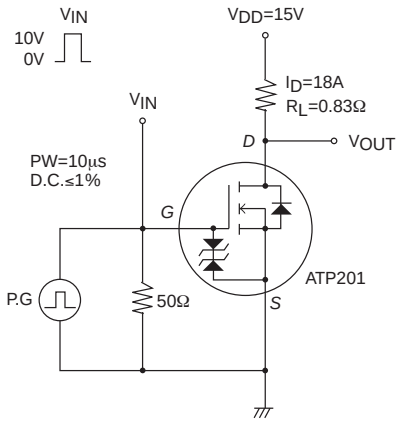
Electrical Connection



Electrical Characteristics at Ta=25°C

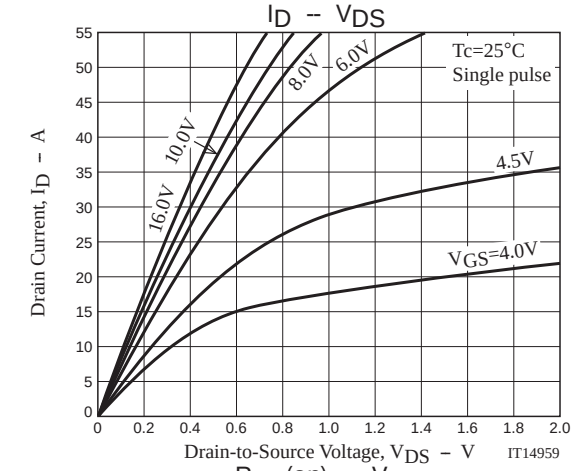
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	I_D=1mA, V_{GS}=0V	30			V
Zero-Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1	μA
Gate-to-Source Leakage Current	I_{GSS}	V_{GS}=±16V, V_{DS}=0V			±10	μA
Cutoff Voltage	$V_{GS}(off)$	V_{DS}=10V, I_D=1mA	1.2		2.6	V
Forward Transfer Admittance	| yfs |	V_{DS}=10V, I_D=18A		24		S
Static Drain-to-Source On-State Resistance	$R_{DS}(on)1$	I_D=18A, V_{GS}=10V		13	17	mΩ
	$R_{DS}(on)2$	I_D=9A, V_{GS}=4.5V		23	33	mΩ
Input Capacitance	Ciss	V_{DS}=10V, f=1MHz		985		pF
Output Capacitance	Coss			180		pF
Reverse Transfer Capacitance	Crss			100		pF
Turn-ON Delay Time	$t_d(on)$	See specified Test Circuit.		10		ns
Rise Time	t_r			230		ns
Turn-OFF Delay Time	$t_d(off)$			51		ns
Fall Time	t_f			39		ns
Total Gate Charge	Qg	V_{DS}=15V, V_{GS}=10V, I_D=35A		17		nC
Gate-to-Source Charge	Qgs			4.7		nC
Gate-to-Drain “Miller” Charge	Qgd			2.8		nC
Diode Forward Voltage	V_{SD}	I_S=35A, V_{GS}=0V		0.97	1.2	V

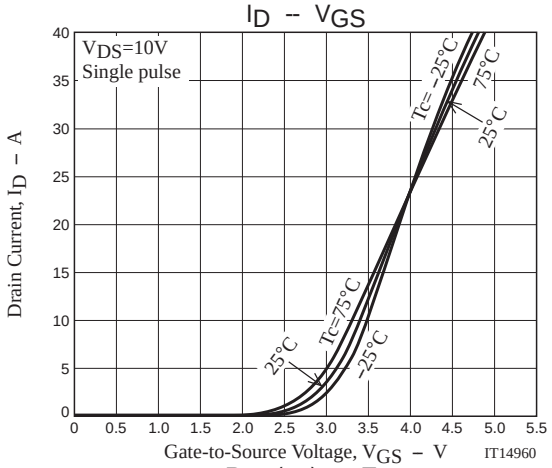
Switching Time Test Circuit

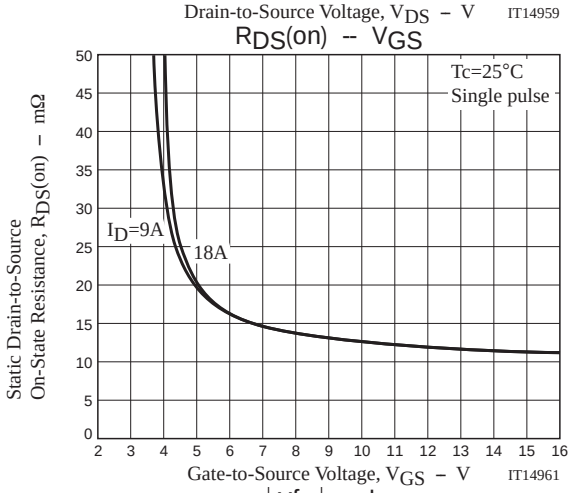


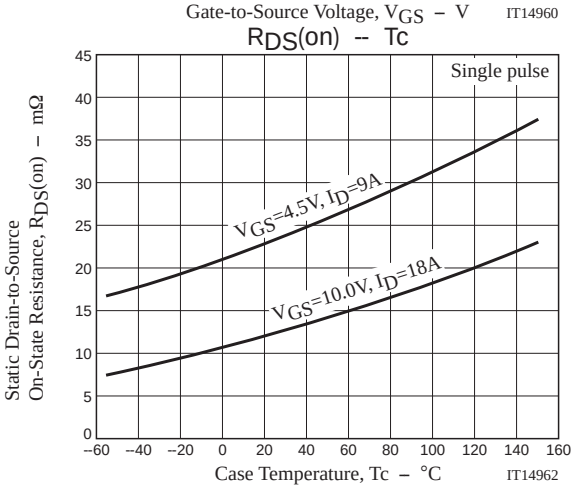
Ordering Information

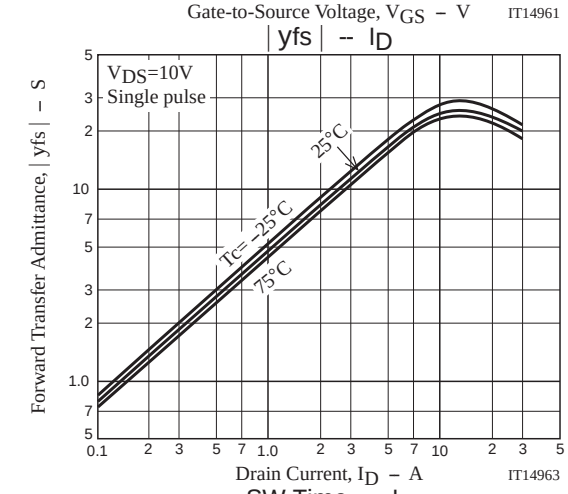
Device	Package	Shipping	memo
ATP201-TL-H	ATPAK	3,000pcs./reel	Pb Free and Halogen Free

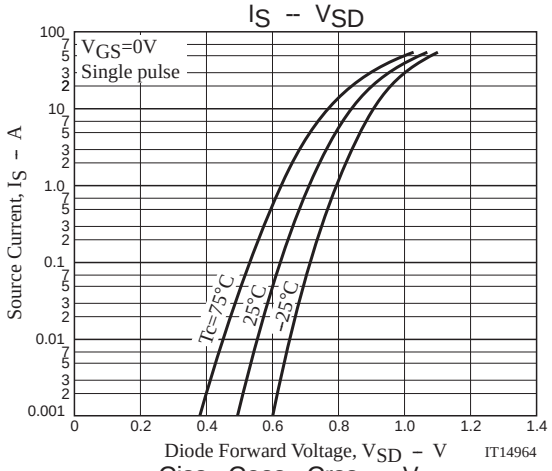


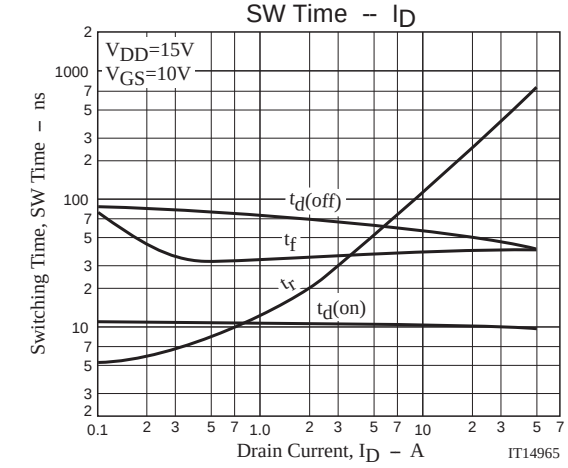


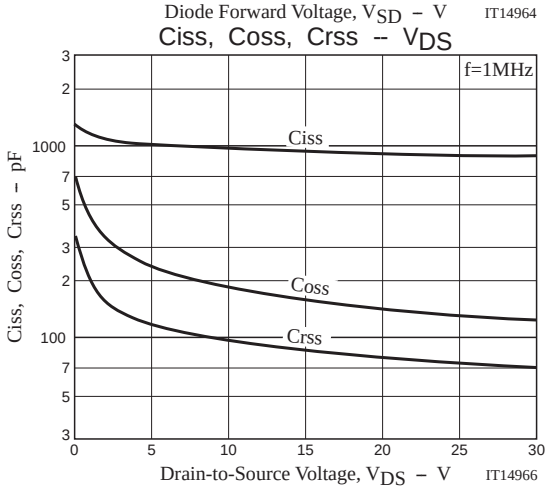


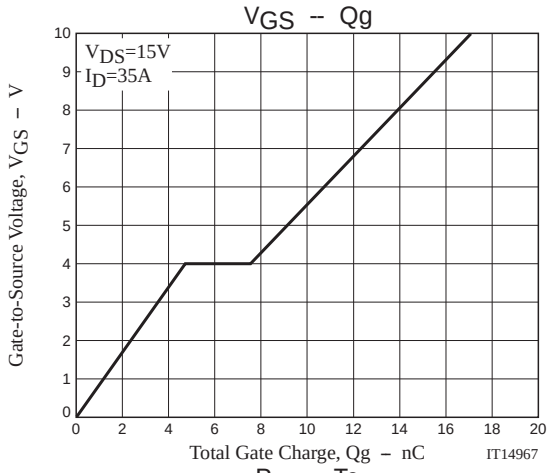


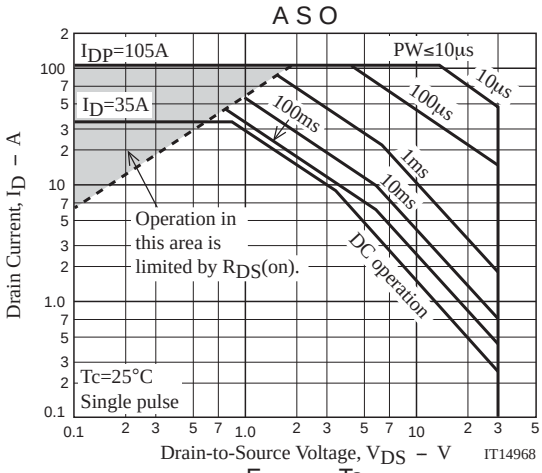


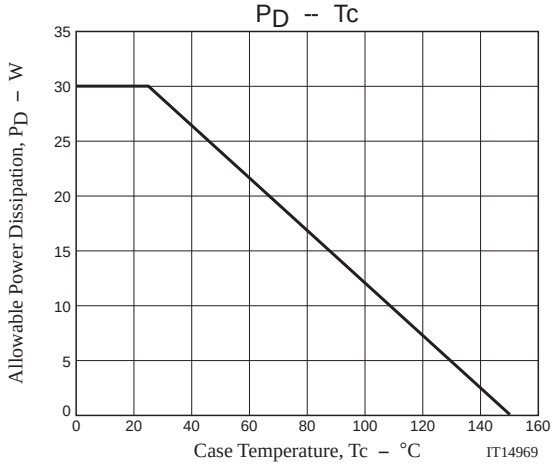


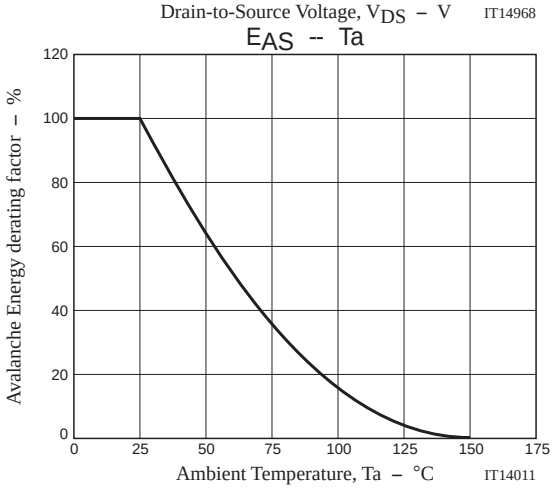












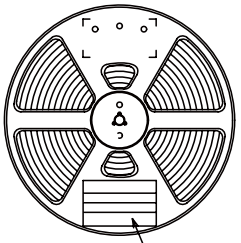
Taping Specification

ATP201-TL-H

1. Packing Format (TL)

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	INNER BOX SD-C-18	OUTER BOX SD-A-18
ATPAK	ATP	3,000	3,000	15,000	1 reels contained Dimensions:mm (external) 340×340×28	5 inner boxes contained Dimensions:mm (external) 355×355×165

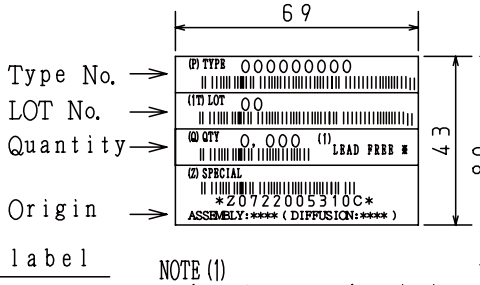
Packing method



Reel label

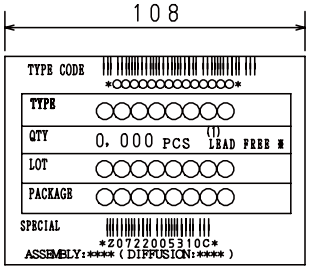
Reel label, Inner box label

(unit:mm)



Outer box label

It is a label at the time of factory shipments. The form of a label may change in physical distribution process.



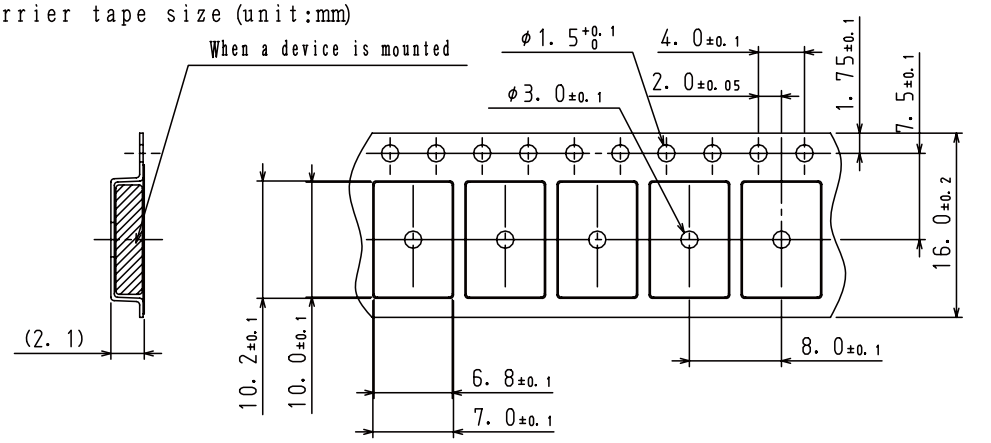
NOTE (1)

The LEAD FREE ※ description shows that the surface treatment of the terminal is lead free.

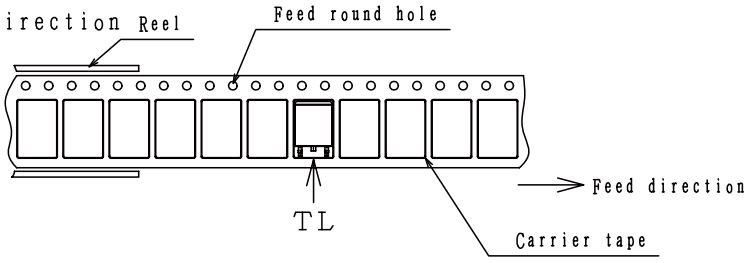
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)



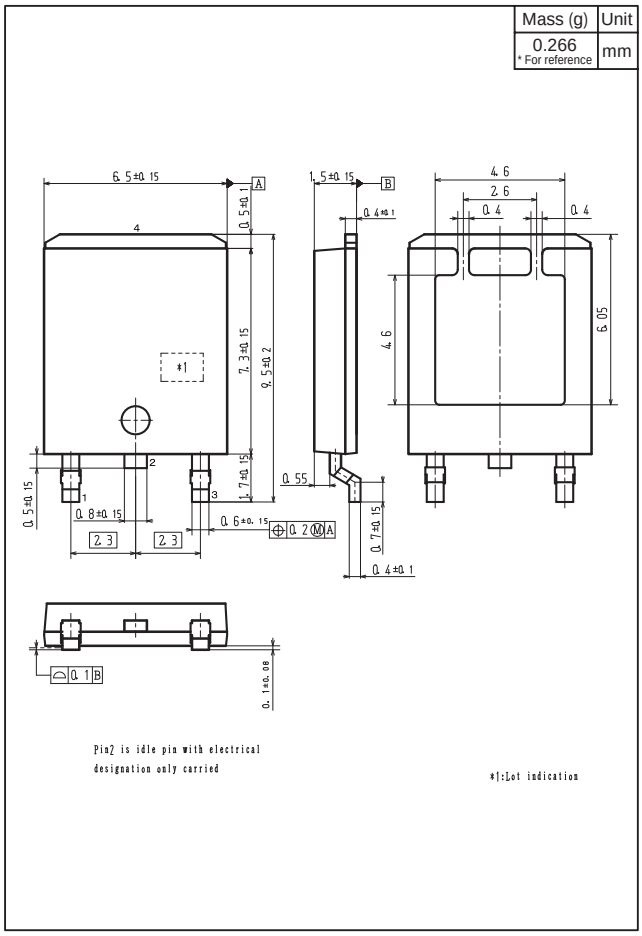
2-2. Device placement direction



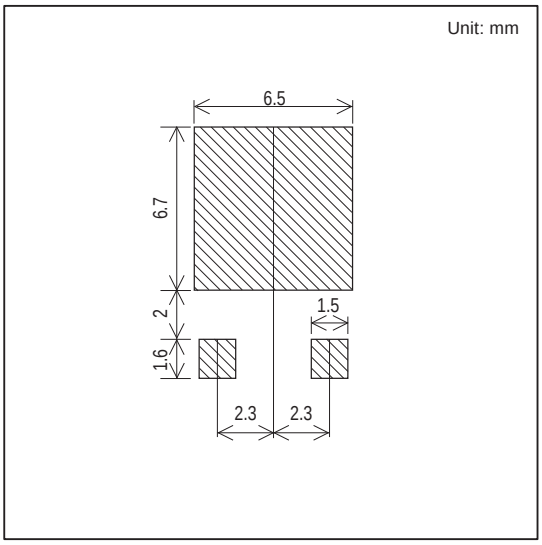
The one erectrode terminals on feed hole side····TL

Outline Drawing

ATP201-TL-H



Land Pattern Example



Note on usage : Since the ATP201 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

This catalog provides information as of June, 2012. Specifications and information herein are subject to change without notice.